



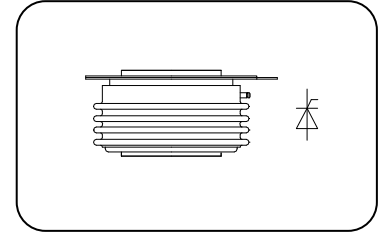
Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$ **300A**
 V_{DRM}/V_{RRM} **1200~1800V**
 t_q **16~35μs**
 I_{TSM} **4.3kA**
 I^2t **92 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, T _c =55°C	125		300	490	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM}&V_{RRM}$, tp=10ms $V_{DSM}&V_{RSM}=V_{DRM}&V_{RRM}+100V$	125	1200		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	$V_D=V_{DRM}$ $V_R=V_{RRM}$	125			30	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			4.3	kA
I^2t	I ² T for fusing coordination	$V_R=0.6V_{RRM}$				92	A ² S*10 ³
V_{TO}	Threshold voltage		125			1.50	V
r_T	On-state slop resistance					0.66	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=900A, F=10kN$	25			3.0	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, $I_{TM}=(2-3)I_{T(AV)}$, t=5s Gate pulse, t _r ≤0.5μs, I _{GM} =1.5A, f=50Hz	125			300	A/μs
Q _{rr}	Recovery charge	$I_{TM}=1000A, tp=1000μs$, di/dt=-20A/μs, V _R =100V	125		200		μC
t _q	Circuit commutated turn-off time	$I_{TM}=1000A, tp=1000μs$, V _R =100V dv/dt=30V/μs, di/dt=-20A/μs	125	16		35	μs
I_{GT}	Gate trigger current		25	40		250	mA
V_{GT}	Gate trigger voltage	V _A =12V, I _A =1A		0.9		2.5	V
I_H	Holding current			20		300	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 18kN				0.035	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.008	
F _m	Mounting force			8		12	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				260		g
Outline	KT40cT						

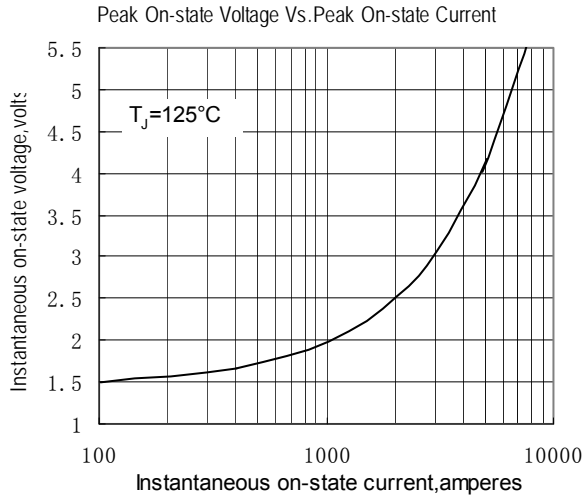


Fig.1

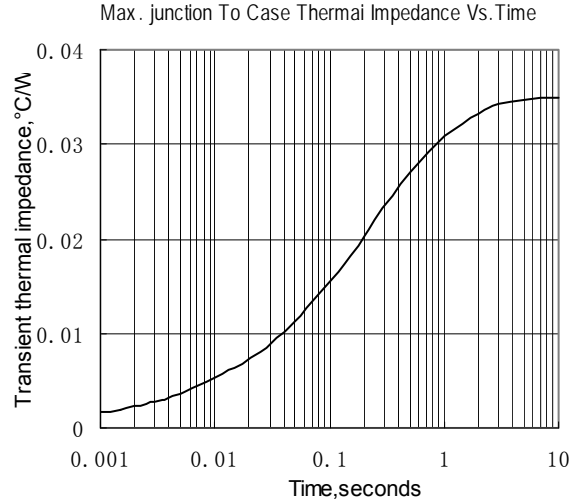


Fig.2

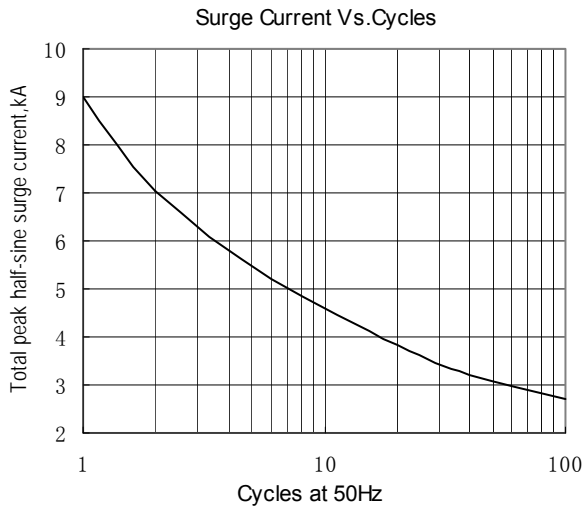


Fig.3

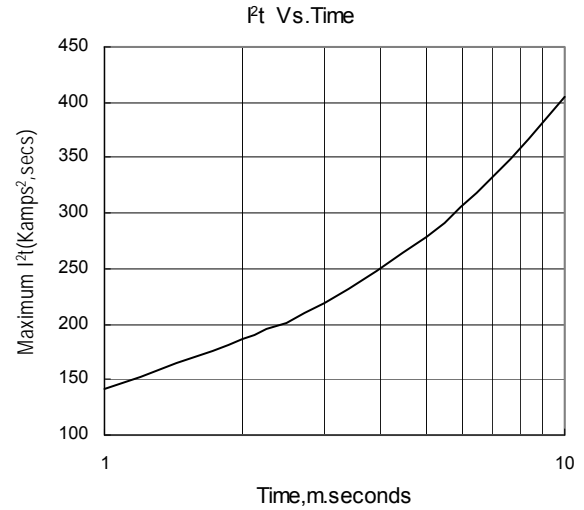


Fig.4

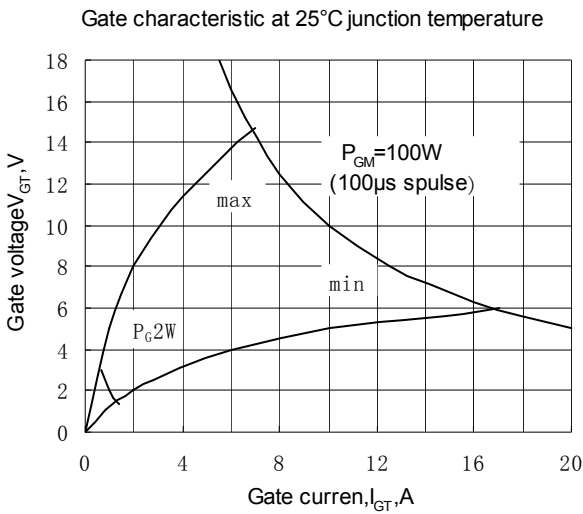


Fig.5

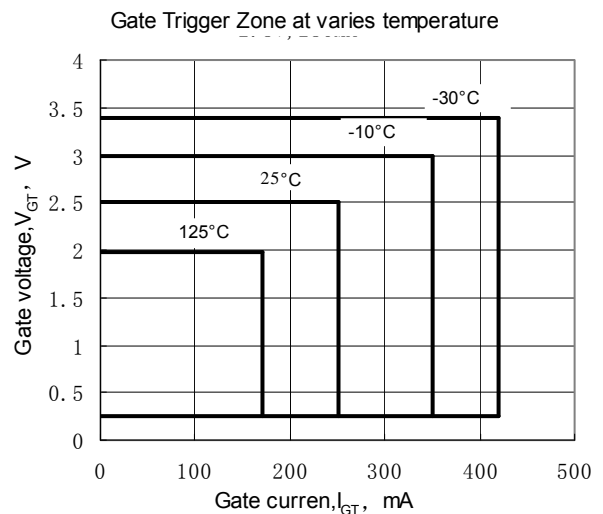
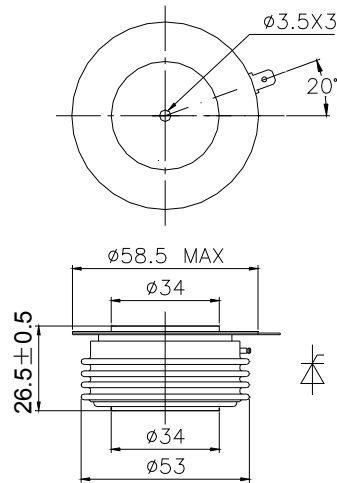


Fig.6



Outline:

图4-KT40cT



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